



YJP100GP06H

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

| | |
|-----------------------------------|--------|
| V_{DS} | -60 V |
| I_D | -100 A |
| $R_{DS(ON)}$ (at $V_{GS}=-10V$) | 8.8m |
| $R_{DS(ON)}$ (at $V_{GS}=-6V$) | 10m |
| 100% EAS Tested | |
| 100% V_{DS} Tested | |

General Description

Split gate trench MOSFET technology
High density cell design for low $R_{DS(ON)}$
Excellent stability and uniformityera(ty06.34 T9(r)13(m)-6(6.04 842.04



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Electrical Characteristics ($T_J=25$ unless otherwise noted)



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Typical Electrical and Thermal Characteristics Diagrams

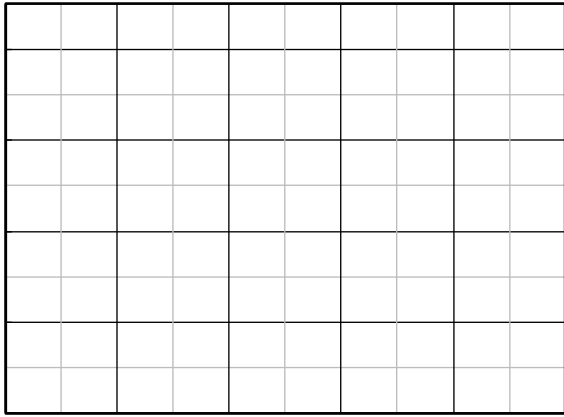


Figure 1. Output Characteristics

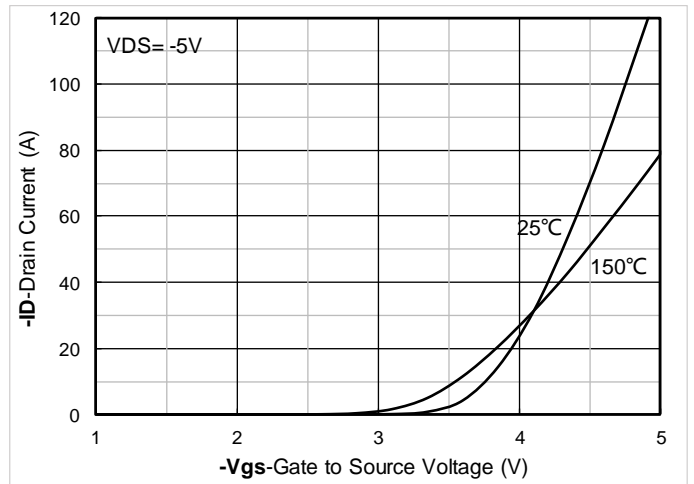


Figure 2. Transfer Characteristics

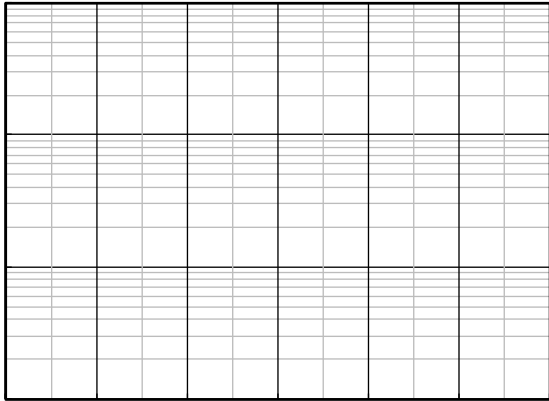


Figure 3. Capacitance Characteristics

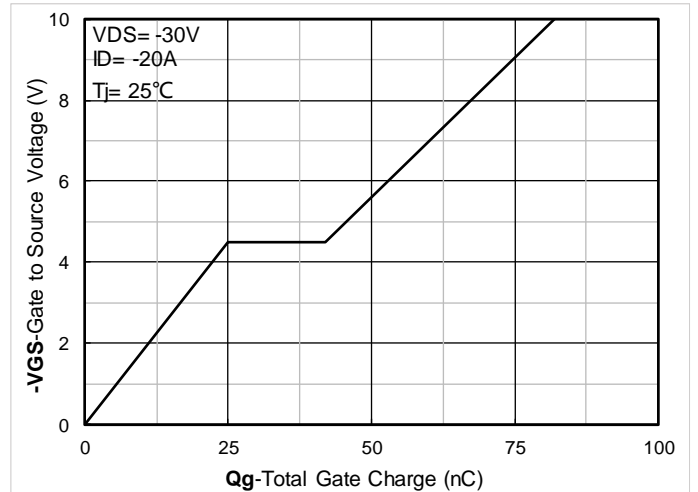


Figure 4. Gate Charge

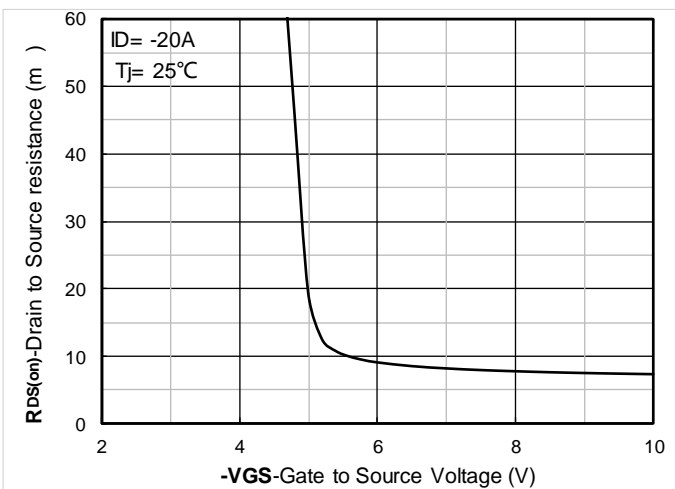


Figure 5. On-Resistance vs Gate to Source Voltage

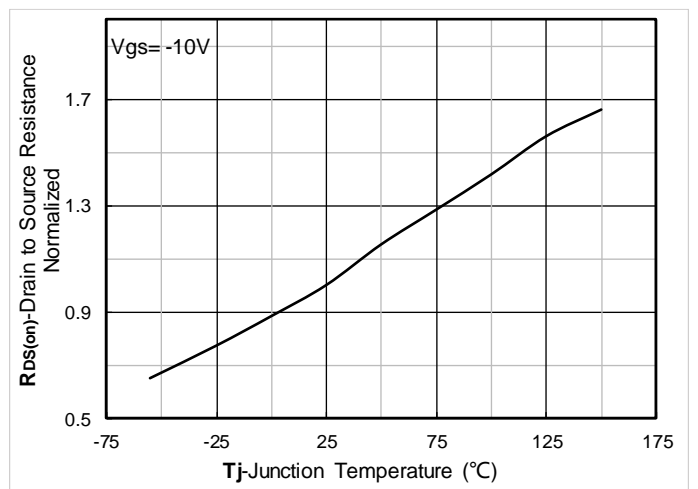


Figure 6. Normalized On-Resistance



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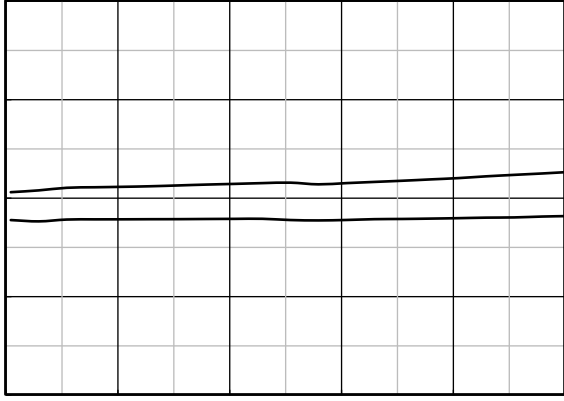


Figure 7. $R_{DS(on)}$ VS Drain Current

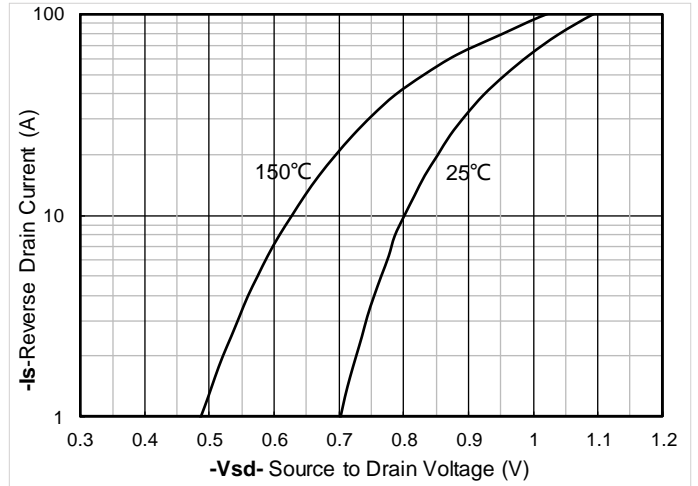


Figure 8. Forward characteristics of reverse diode

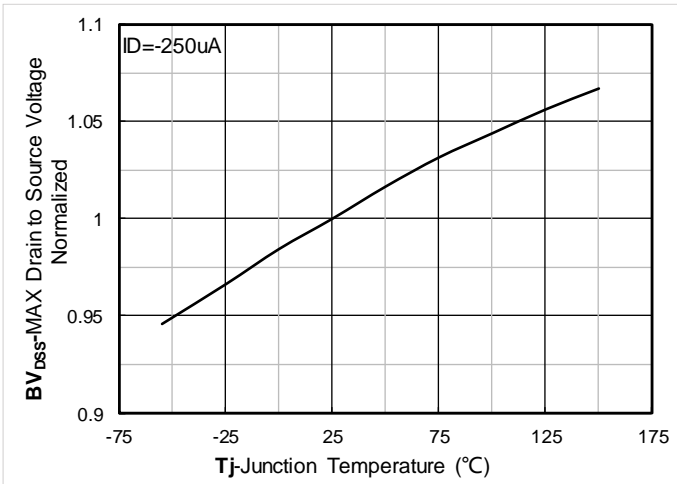


Figure 9. Normalized breakdown voltage

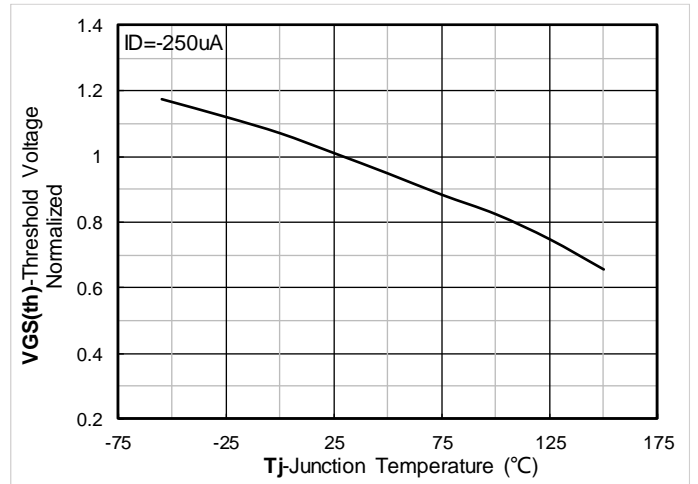


Figure 10. Normalized Threshold voltage

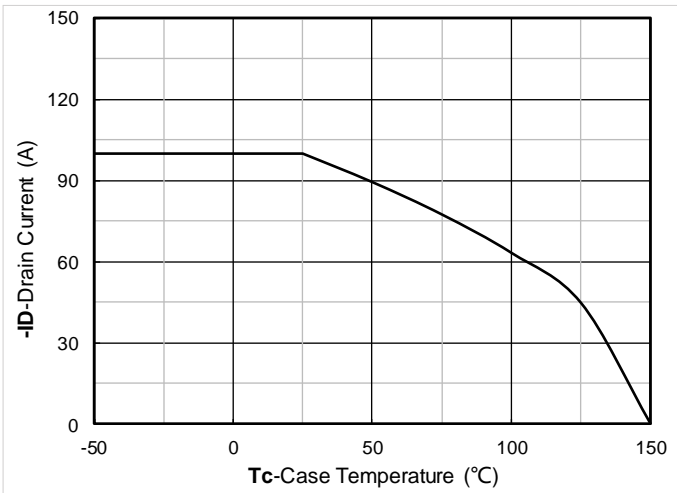


Figure 11. Current dissipation

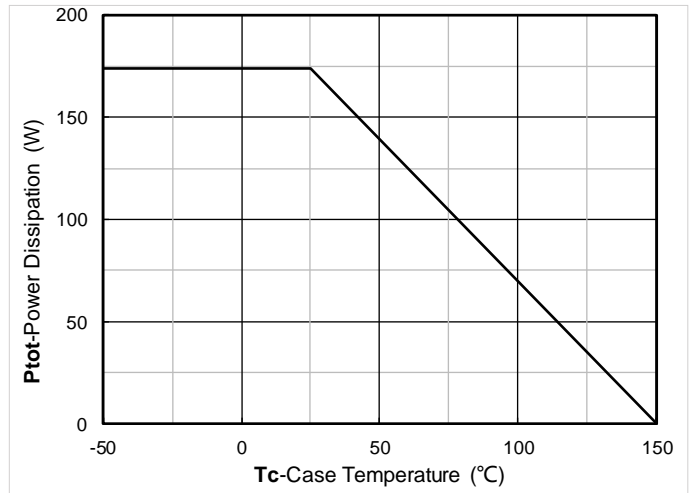


Figure 12. Power dissipation

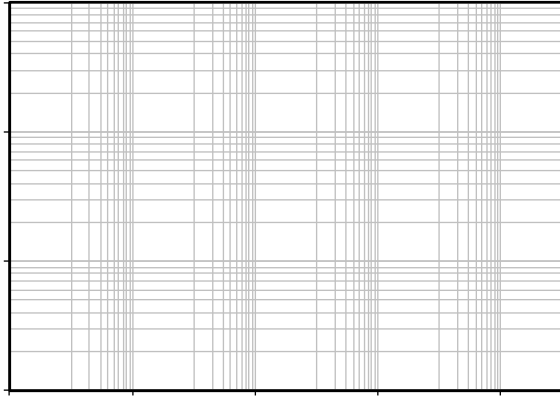


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



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